

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("6611025").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/26 05:18
L2	1	"6476449".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:19
L3	1	"6274908".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:19
L4	1	"6236073".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:19
L5	1	"6225166".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:20
L6	1	"6215156".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:20
L7	1	"6157065".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:20
L8	1	"6153913".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:20
L9	1	"6064095".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:20
L10	1	"6057555".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:20
L11	1	"6046087".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:21
L12	1	"6025631".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:21
L13	1	"5973382".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:21
L14	1	"5973363".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:22
L15	1	"5940258".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:22
L16	1	"5937298".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:22
L17	1	"5932918".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:22
L18	1	"5747853".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:23
L19	1	"5721439".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:23
L20	1	"5610790".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:24
L21	1	"5311391".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:30
L22	1	"5283449".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:31

L23	1	"5264723".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:31
L24	1	"5223444".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:31
L25	1	"5210442".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:31
L26	1	"5124877".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:31
L27	1	"5041889".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:32
L28	1	"5548134".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:32
L29	1	"5378919".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:32
L30	1	"5283499".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:33
L31	1	"5248892".PN.	USPAT; USOCR	OR	ON	2005/11/26 05:33
L32	557	('protection' or 'dummy') with 'transistor' and 'triggered' with 'transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 06:04
L33	218	('protection' or 'dummy') with 'transistor' same 'triggered' with 'transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 05:41
L34	209	'protection' with 'transistor' same 'triggered' with 'transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 05:58
L35	4	((("5,744,842") or ("6,072,219"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/26 05:58
L36	21	'ESD' and 'protection' and 'dummy gate' and ('triggered' or 'triggering') with 'substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 06:13
L37	301	'ESD' and 'protection' and (('triggered' or 'triggering')) with 'substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 06:14
L38	300	'ESD' same 'protection' and (('triggered' or 'triggering')) with 'substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 06:14

L39	190	'ESD' same 'protection' same ('triggered' or 'triggering') with 'substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 06:36
L40	0	'ESD' same 'protection' and 'dummy gater' same ('coupled' or 'connecting' or 'coupling') with 'substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 06:37
L41	6	'ESD' same 'protection' and 'dummy gate' same ('coupled' or 'connecting' or 'coupling') with 'substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 07:24
L42	2	("5744842").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/26 06:44
L43	179	'CMOS' and 'substrate' with 'triggered'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 06:47
L44	85	'dummy gate' same 'protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 07:25
L45	28	'dummy gate' same 'ESD protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/26 07:25
S1	826	@ad<="20040329" and (257/328).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 11:02
S2	219	@ad<="20040329" and (438/212).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:48
S3	635	@ad<="20040329" and (438/268).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:49
S4	1908	@ad<="20040329" and (257/355-356).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:50

S5	463	@ad<="20040329" and (257/357). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 10:41
S6	58	'NEC' and 'ando takeshi'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:51
S7	1954	@ad<="20040329" and (257/369). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:53
S8	2215	@ad<="20040329" and 'CMOS' same 'protection' same 'circuit'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:37
S9	1296	@ad<="20040329" and 'CMOS' with 'protection' with 'circuit'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:02
S10	777	@ad<="20040329" and 'CMOS' with 'protection circuit'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:02
S11	3	@ad<="20040329" and 'CMOS' with 'protection circuit' and 'output electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:04
S12	40	@ad<="20040329" and 'CMOS' with 'protection' and 'surge' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 08:26
S13	235	@ad<="20040329" and 'CMOS' and 'protection' and 'surge' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:05
S14	1150	@ad<="20040329" and 'CMOS' and 'ESD' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:05
S15	422	@ad<="20040329" and 'CMOS' same 'ESD' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 09:43

S16	283	@ad<="20040329" and 'CMOS' with 'ESD' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:06
S17	1833	@ad<="20040329" and (361/56). cccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:49
S18	1	"6385028".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:24
S19	1	"6249410".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:25
S20	1	"6064249".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:26
S21	1400	@ad<="20040329" and (361/111). cccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:41
S22	1	"6266222".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:28
S23	1	"6130811".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:28
S24	1	"6034397".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:29
S25	1	"6080612".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:33
S26	1	"5963409".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:33
S27	1	"5086365".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:34
S28	1	"5910874".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:38
S29	1	"5729419".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S30	1	"5644459".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S31	1	"5086365".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S32	1	"5644459".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S33	1	"5499152".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S34	8	@ad<="20040329" and 'Electrostatic damage protection circuit'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:44

S36	1004	@ad<="20040329" and 'ESD protection circuit' and 'CMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:44
S37	830	@ad<="20040329" and 'ESD protection circuit' and 'CMOS' and 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:44
S38	1	@ad<="20040329" and 'ESD protection circuit' and 'CMOS' and 'output electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:45
S39	86	@ad<="20040329" and 'CMOS' and 'protection transistor' and 'output transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:48
S40	1	"6066879".PN.	USPAT; USOCR	OR	ON	2005/06/06 08:35
S41	1	"5918127".PN.	USPAT; USOCR	OR	ON	2005/06/06 08:36
S42	1	"6080612".PN.	USPAT; USOCR	OR	ON	2005/06/06 08:38
S43	1	"5610790".PN.	USPAT; USOCR	OR	ON	2005/06/06 08:38
S44	1	"5986867".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:00
S45	1	"5499152".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:00
S46	1	"6388315".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:12
S47	1	"6281554".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:12
S48	1	"6066879".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:38
S49	1	@ad<="20040329" and 'CMOS' and 'protection' and 'outout' and 'output pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 09:44
S51	7	@ad<="20040329" and 'CMOS' and 'protection MOS' and 'output MOS' and 'output pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 09:45
S52	139	@ad<="20040329" and 'CMOS' and 'protection' with 'MOS' and 'output' with 'MOS' and 'output pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:12

S53	420	@ad<="20040329" and 'CMOS' same 'output' same 'ESD' same 'protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:26
S54	356	@ad<="20040329" and 'CMOS' same 'output' same 'ESD' protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:28
S55	86	@ad<="20040329" and 'CMOS' same 'output pad' same 'ESD' protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:28
S56	0	@ad<="20040329" and 'CMOS' same 'output electrode' same 'ESD' protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:29
S57	2	@ad<="20040329" and 'CMOS' and 'output electrode' and 'ESD' protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:29
S58	5	@ad<="20040329" and 'CMOS' same 'protection' same 'circuit' and 'dummy transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:40
S59	9	'Ichikawa Kenji' and 'oki'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:03
S60	2	@ad<="20040329" and 'CMOS' and 'improved electrostatic breakdown resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:44
S61	23	@ad<="20040329" and 'CMOS' and 'electrostatic breakdown resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:44
S62	76	@ad<="20040329" and 'ESD' and 'protection transistor' and 'output transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:48
S63	230	Ichikawa-Kenji.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:05

S64	3	Ichikawa-Kenji.in. and 'ESD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:04
S65	13	Ichikawa-Kenji.in. and 'semiconductor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:06
S66	0	'surge current' same 'ON current' same 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:07
S67	0	'surge current' and 'ON current' same 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:07
S68	0	'surge current' and 'ON current' and 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:07
S69	22	'surge current' same 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:13
S70	1	"6080612".PN.	USPAT; USOCR	OR	ON	2005/06/06 11:11
S71	1	'protection transistor' and 'low' with ('electrostatic discharge' or 'ESD') with 'resistance' and 'electrode pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:15
S72	51	'protection transistor' and 'low' with ('electrostatic discharge' or 'ESD') with 'resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:15
S73	411	@ad<="20040329" and 'output' with ('electrode' or 'pad') and 'MOS' with 'protection' and 'MOS' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 10:15
S74	21	@ad<="20040329" and 'output' with ('electrode' or 'pad') and 'MOS' near 'protection' and 'MOS' near 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 08:14
S75	1	"6326666".PN.	USPAT; USOCR	OR	ON	2005/06/07 08:37
S76	1	"6281554".PN.	USPAT; USOCR	OR	ON	2005/06/07 08:38

S77	1	"6278160".PN.	USPAT; USOCR	OR	ON	2005/06/07 08:39
S78	1	"6207996".PN.	USPAT; USOCR	OR	ON	2005/06/07 08:39
S79	70	@ad<="20040329" and 'input/output' or 'I/O' and 'protection transistor' and 'output transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 09:48
S80	1	@ad<="20040329" and 'input/output' or 'I/O' and 'MOS protection' and 'MOS output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 09:22
S81	10	@ad<="20040329" and 'protection transistor' same 'gate' same 'connect' same 'substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:09
S82	1	"6232220".PN.	USPAT; USOCR	OR	ON	2005/06/07 09:32
S83	8	@ad<="20040329" and 'input/output' or 'I/O' and 'protection transistor' and 'positive surge'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 09:48
S84	2	"20040195625"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 10:00
S85	107	@ad<="20040329" and 'CMOS' same 'protection' same 'SOI'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:03
S86	84	@ad<="20040329" and 'ESD protection' same 'SOI' same 'bulk'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:03
S87	76	@ad<="20040329" and 'ESD protection' same 'SOI' with 'bulk'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:15
S88	40	@ad<="20040329" and 'ESD protection' with 'SOI' with 'bulk'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:03
S89	227	@ad<="20040329" and 'SOI substrate' with 'bulk substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:16

S90	115	@ad<="20040329" and 'CMOS' and 'SOI substrate' with 'bulk substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:16
S91	24	@ad<="20040329" and 'CMOS' same 'SOI substrate' with 'bulk substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:18
S92	7	@ad<="20040329" and 'CMOS' and 'SOI substrate' with 'bulk substrate' and 'ESD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:18
S93	44	@ad<="20040329" and (361/56). ccls. and 'SOI' and 'ESD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:50
S94	114	@ad<="20040329" and 'SOI' and 'ESD' and 'CMOS' and 'clamp'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:54
S95	772	@ad<="20040329" and 'ESD' and 'CMOS' and 'clamp'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:54
S96	1	"6204537".PN.	USPAT; USOCR	OR	ON	2005/06/07 12:02
S97	1	"6091592".PN.	USPAT; USOCR	OR	ON	2005/06/07 12:02
S98	154	@ad<="20040329" and 'CMOS' and ('protection' or 'dummy') with 'MOS' and 'output' with 'MOS' and 'output pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:15
S99	19	@ad<="20040329" and 'CMOS' same 'charge ' with 'protection' and 'output pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 09:51
S10 0	1	"5679972".PN.	USPAT; USOCR	OR	ON	2005/11/23 10:01
S10 1	1	"6369998".PN.	USPAT; USOCR	OR	ON	2005/11/23 10:34
S10 2	472	@ad<="20040329" and (257/357). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 10:48

S10 3	14	(("6236087") or ("3878551") or ("5594279") or ("5140401") or ("5786617") or ("5959820") or ("6122704")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/23 10:49
S10 4	35	@ad<="20040329" and 'trigger transistor' and 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 11:01
S10 6	423	@ad<="20040329" and (361/56). ccls. and 'ESD' and 'CMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:24
S10 7	1	"6204537".PN.	USPAT; USOCR	OR	ON	2005/11/23 11:03
S10 8	1	"6091592".PN.	USPAT; USOCR	OR	ON	2005/11/23 11:03
S10 9	1	"6072219".PN.	USPAT; USOCR	OR	ON	2005/11/23 11:04
S11 0	1	"6069782".PN.	USPAT; USOCR	OR	ON	2005/11/23 11:05
S11 1	1	"6043967".PN.	USPAT; USOCR	OR	ON	2005/11/23 11:05
S11 2	1	"6040603".PN.	USPAT; USOCR	OR	ON	2005/11/23 11:05
S11 3	1	"5982600".PN.	USPAT; USOCR	OR	ON	2005/11/23 11:05
S11 4	1	"6081015".PN.	USPAT; USOCR	OR	ON	2005/11/23 12:05
S11 5	10	@ad<="20040329" and 'protection transistor' same 'gate' same 'connect' same 'substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:09
S11 6	385	@ad<="20040329" and 'Ker' and 'ESD' and 'CMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:15
S11 7	192	@ad<="20040329" and 'Ker' and 'ESD' and 'CMOS' and 'clamp'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:14
S11 8	0	@ad<="20040329" and 'ESD' and 'trigger transistor' and 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:14

S11 9	12	@ad<="20040329" and 'ESD' and 'trigger transistor' and 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:14
S12 0	0	@ad<="20040329" and 'ESD' and 'CMOS' and 'clamp' and 'stand off'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:16
S12 1	4	@ad<="20040329" and 'ESD' and 'clamp' and 'stand-off'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:18
S12 2	36	@ad<="20040329" and 'ESD' and 'stand-off'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:18
S12 3	47	@ad<="20040329" and 'ESD' and 'stand off'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:18
S12 4	33	@ad<="20040329" and 'Electrostatic discharge clamp'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:29
S12 5	69	@ad<="20040329" and 'CDM' with 'ESD' with 'protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/23 12:29
S12 6	1	"6326666".PN.	USPAT; USOCR	OR	ON	2005/11/23 12:44
S12 7	1	"6281554".PN.	USPAT; USOCR	OR	ON	2005/11/23 12:44
S12 8	1	"6278160".PN.	USPAT; USOCR	OR	ON	2005/11/23 12:45
S12 9	1	"6207996".PN.	USPAT; USOCR	OR	ON	2005/11/23 12:45
S13 0	1	"6207996".PN.	USPAT; USOCR	OR	ON	2005/11/23 12:47
S13 1	1	"6114731".PN.	USPAT; USOCR	OR	ON	2005/11/23 12:47